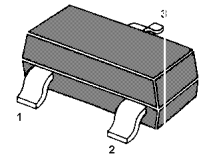
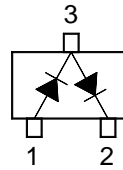


# 1SS226-AH

## Silicon Epitaxial Planar Switching Diode

### Features

- Small package
- Low forward voltage
- Fast reverse recovery time
- Small total capacitance
- AEC-Q101 Qualified and PPAP Capable
- Halogen and Antimony Free(HAF), RoHS compliant



Marking Code: **A7**  
1. Anode 1 2. Cathode 2  
3. Anode 2 / Cathode 1  
SOT-23 Plastic Package

### Applications

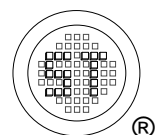
- Ultra high speed switching application

### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	$V_{RM}$	85	V
Reverse Voltage	$V_R$	80	V
Average Rectified Forward Current	$I_{F(AV)}$	100	mA
Maximum Peak Forward Current	$I_{FM}$	300	mA
Non-repetitive Peak Forward Surge Current (10 ms)	$I_{FSM}$	2	A
Power Dissipation	$P_{tot}$	350	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 100\text{ mA}$	$V_F$	1.2	V
Reverse Current at $V_R = 80\text{ V}$	$I_R$	0.5	$\mu\text{A}$
Total Capacitance at $V_R = 0$ , $f = 1\text{ MHz}$	$C_T$	3	pF
Reverse Recovery Time at $I_F = 10\text{ mA}$	$t_{rr}$	4	ns



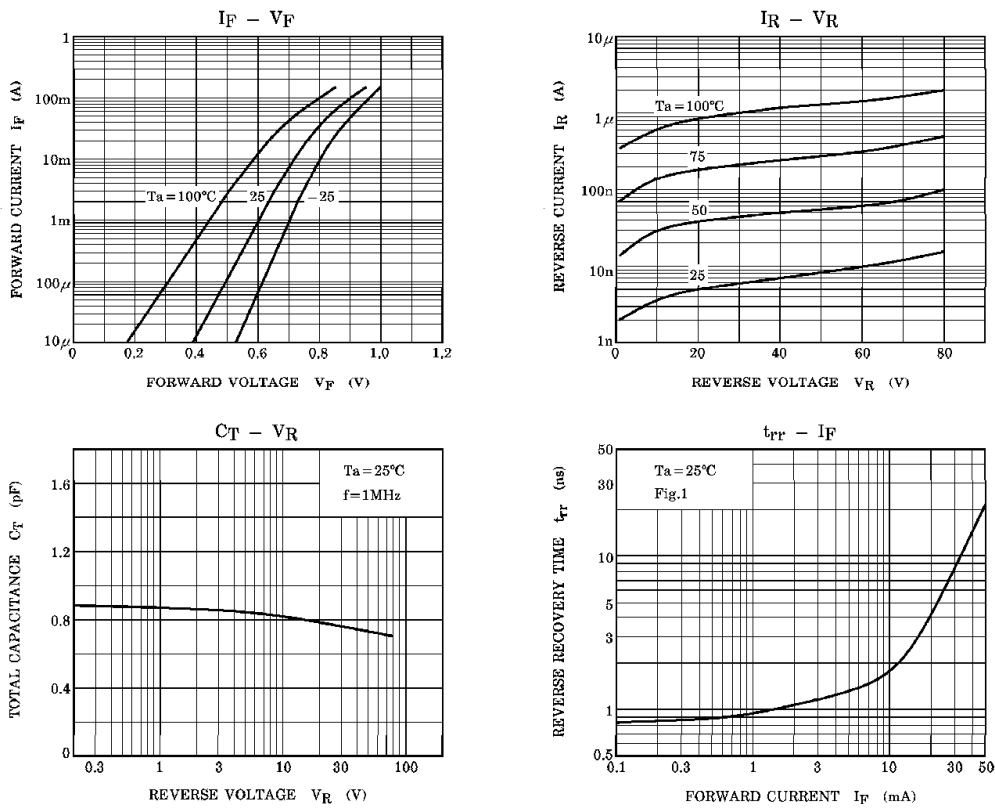


Fig.1 Reverse recovery time ( $t_{rr}$ ) test circuit

